

# TO-92MOD Plastic-Encapsulated Transistors

## 2SA966 TRANSISTOR (PNP)

### FEATURE

Power dissipation

$P_{CM}$ : 0.9 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$  : -30 V

Operating and storage junction temperature range

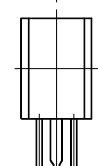
$T_J, T_{stg}$ : -55°C to +150°C

### TO-92MOD

1. Emitter



2. Collector



3. Base

1 2 3

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1mA, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -30V, I_E = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$		-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -500mA$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -0.03A$		-2	V
Base-emitter voltage	$V_{BE}$	$I_C = -500mA, V_{CE} = -2V$		-1	V
Transition frequency	$f_T$	$V_{CE} = -2V, I_C = -500mA$	100		MHz

### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320